

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC240AP, TC74HC240AF, TC74HC240AFW, TC74HC241AP TC74HC241AF, TC74HC244AP, TC74HC244AF, TC74HC244AFW

OCTAL BUS BUFFER

TC74HC240AP/AF/AFW **INVERTED, 3-STATE OUTPUTS**
 TC74HC241AP/AF **NON-INVERTED, 3-STATE OUTPUTS**
 TC74HC244AP/AF/AFW **NON-INVERTED, 3-STATE OUTPUTS**

(Note) The JEDEC SOP (FW) is not available in Japan.

The TC74HC240A, 241A and 244A are high speed CMOS OCTAL BUS BUFFERS fabricated with silicon gate CMOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

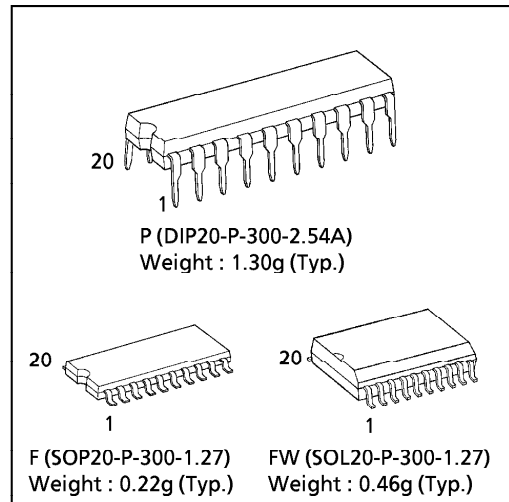
The 74HC240A is an inverting 3-state buffer having two active-low output enables. The TC74HC241A and TC74HC244A are non-inverting 3-state buffers that differ only in that the 241A has one active-high and one active-low output enable, and the 244A has two active-low output enables.

These devices are designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

- High Speed..... $t_{pd} = 10\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Output Drive Capability..... 15 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 6\text{mA}(\text{Min.})$
- Balanced Propagation Delays.... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC}(\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS 240/241/244

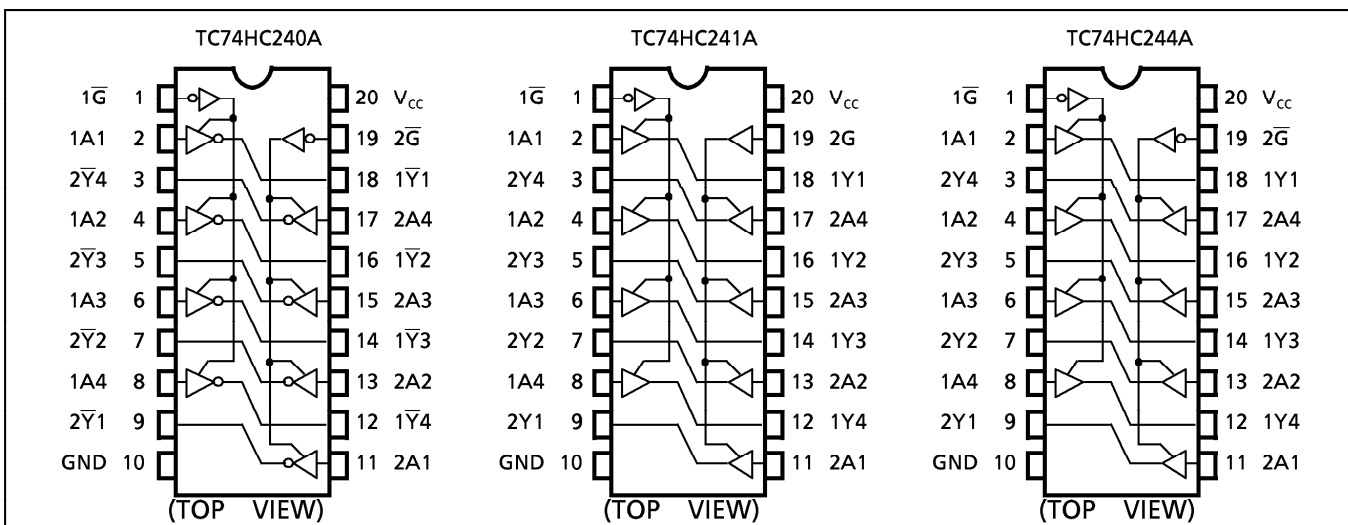


TRUTH TABLE

INPUTS			OUTPUTS	
\bar{G}	G^Δ	A_n	Y_n	$\bar{Y}_n^{\Delta\Delta}$
L	H	L	L	H
L	H	H	H	L
H	L	X	Z	Z

Δ : for TC74HC241A only
 $\Delta\Delta$: for TC74HC240A only
 X : Don't Care
 Z : High Impedance

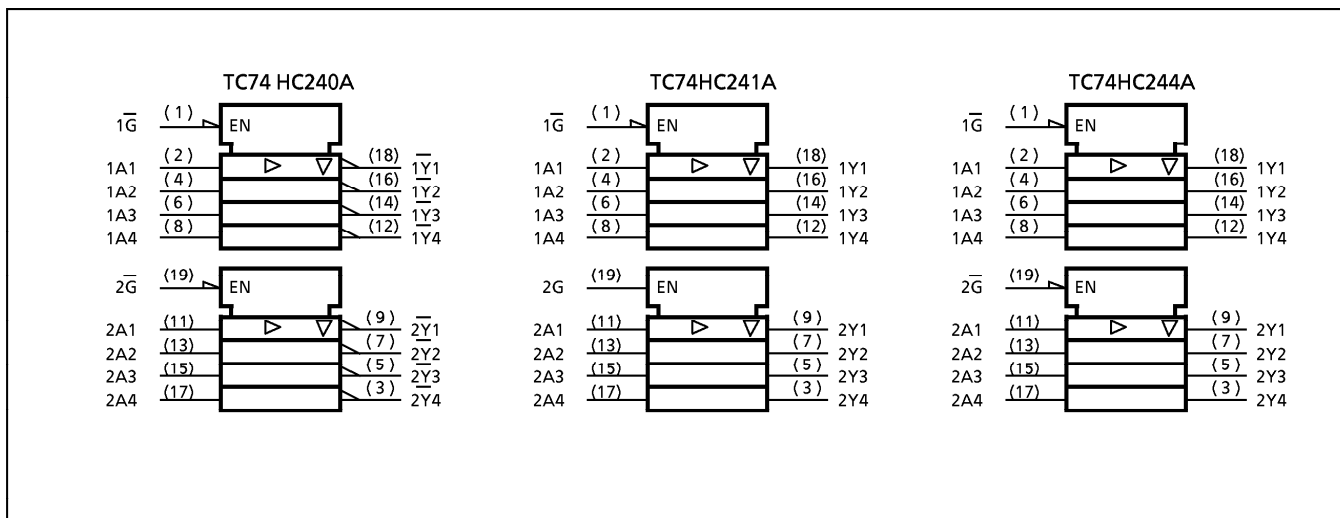
PIN ASSIGNMENT



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IEC LOGIC SYMBOL



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 35	mA
DC V_{CC} / Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~ 1000 ($V_{CC} = 2.0\text{V}$) 0~ 500 ($V_{CC} = 4.5\text{V}$) 0~ 400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
			$I_{OH} = -6\text{mA}$ $I_{OH} = -7.8\text{mA}$	4.5	4.18	4.31	—	4.13	—	
				6.0	5.68	5.80	—	5.63	—	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
			$I_{OL} = 6\text{mA}$ $I_{OL} = 7.8\text{mA}$	4.5	—	0.17	0.26	—	0.33	
				6.0	—	0.18	0.26	—	0.33	
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	6.0	—	—	± 0.5	—	± 5.0	μA	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0		
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0		

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	CL (pF)	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}		50	2.0	—	25	60	—	75	ns
				4.5	—	7	12	—	15	
				6.0	—	6	10	—	13	
Propagation Delay Time	t_{pLH} t_{pHL}		50	2.0	—	36	90	—	115	
				4.5	—	12	18	—	23	
				6.0	—	10	15	—	20	
			150	2.0	—	51	130	—	165	
				4.5	—	17	26	—	33	
				6.0	—	14	22	—	28	
Output Enable time	t_{pZL} t_{pZH}	$R_L = 1\text{k}\Omega$	50	2.0	—	48	125	—	155	
				4.5	—	16	25	—	31	
				6.0	—	14	21	—	26	
			150	2.0	—	63	165	—	205	
				4.5	—	21	33	—	41	
				6.0	—	18	28	—	35	
Output Disable time	t_{pLZ} t_{pHZ}	$R_L = 1\text{k}\Omega$	50	2.0	—	32	125	—	155	
				4.5	—	15	25	—	31	
				6.0	—	14	21	—	26	
Input Capacitance	C_{IN}				—	5	10	—	10	pF
Output Capacitance	C_{OUT}				—	10	—	—		
Power Dissipation Capacitance	$C_{PD}(1)$	TC74HC240A			—	31	—	—	—	
		TC74HC241A / 244A			—	33	—	—	—	

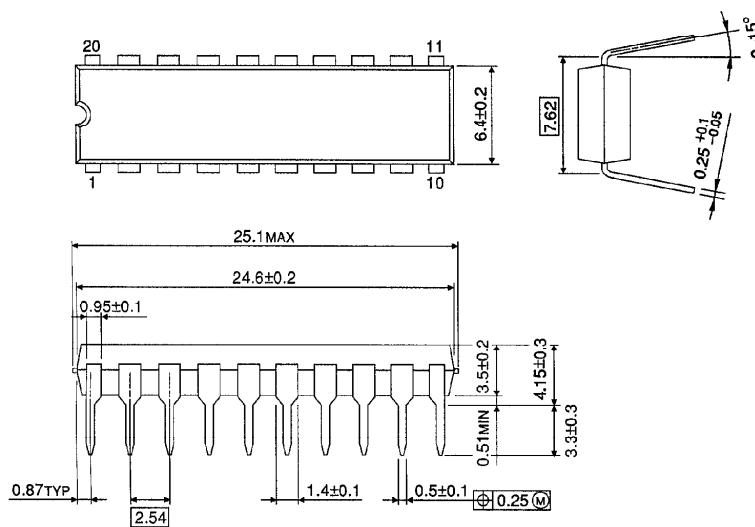
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8 \text{ (per bit)}$$

DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

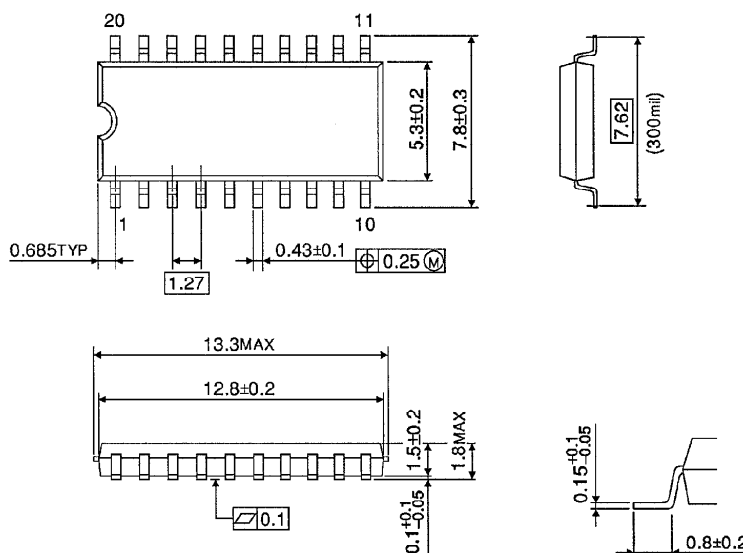
Unit in mm



Weight : 1.30g (Typ.)

SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

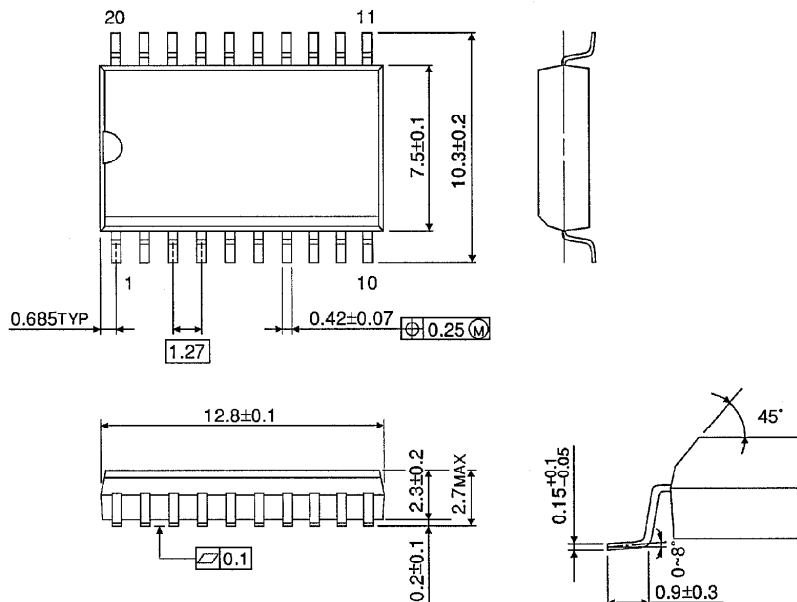


Weight : 0.22g (Typ.)

SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)